

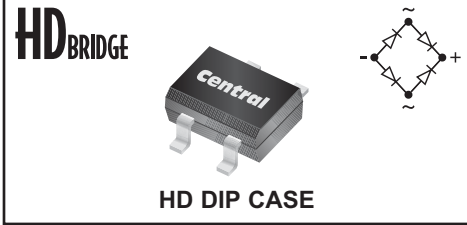
CBRHDSH2-40
SURFACE MOUNT
HIGH DENSITY
2 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH2-40 is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.



MARKING CODE: CSH2

FEATURES:

- Low Leakage Current (20 μ A TYP @ V_{RRM})
- High 2.0A Current Rating
- Low V_F Schottky Diodes (500mV MAX @ $I_F=2.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	I_O	2.0	A
Peak Forward Surge Current	I_{FSM}	30	A
Power Dissipation	P_D	2.0	W
Operating Junction Temperature	T_J	-50 to +125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	50	$^\circ\text{C/W}$

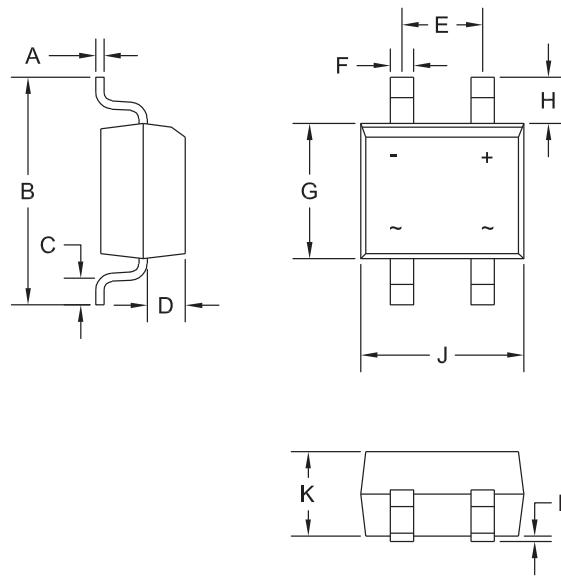
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=40V$	20	50	μA
I_R	$V_R=40V, T_A=100^\circ\text{C}$	5.0	20	mA
V_F	$I_F=2.0A$	450	500	mV
C_J	$V_R=4.0V, f=1.0\text{MHz}$		250	pF

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HD DIP CASE - MECHANICAL OUTLINE



R2

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

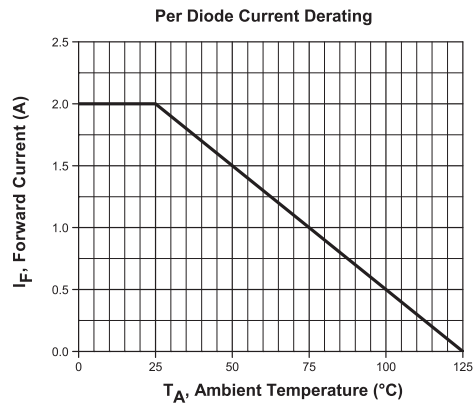
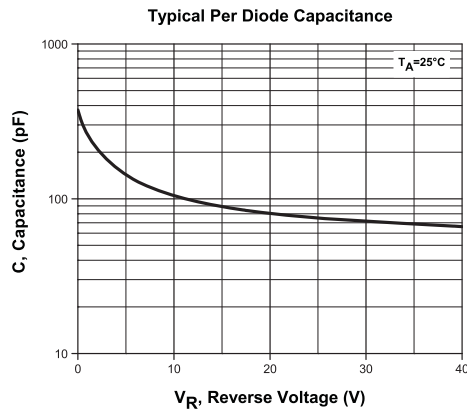
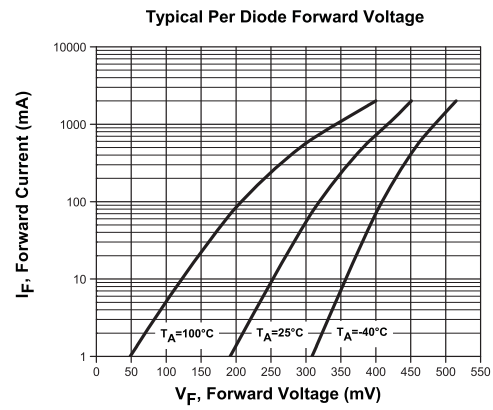
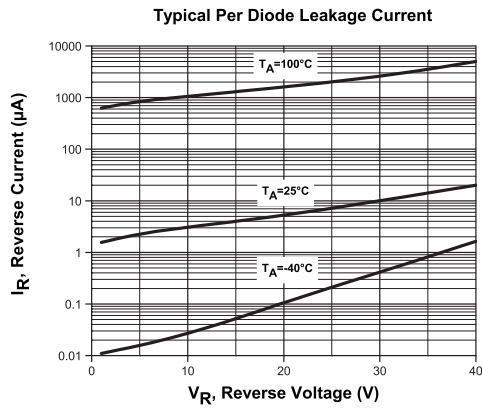
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R4 (4-January 2010)

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TYPICAL ELECTRICAL CHARACTERISTICS



R4 (4-January 2010)